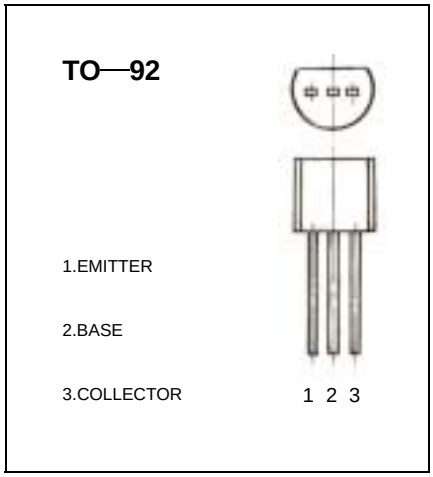
9014

NPN SILICON TRANSISTOR



FEATURES

Power dissipation

P_{CM} : 0.4 W（Tamb=25℃）

Collector current

I_{CM} : 0.1 A

Collector-base voltage

$V_{(BR)CBO}$: 50 V

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= 100 μA, I_E=0	50			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	Ic= 0. 1 mA, I_B=0	45			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100 μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=50 V , I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=35 V , I_B=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 3 V, I_C=0			0.1	μA
DC current gain(note)	$H_{FE\ (1)}$	V_{CE}= 5 V, I_C= 1mA	60		1000	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C= 100mA, I_B= 5 mA			0.3	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C= 100 mA, I_B= 5mA			1	V
Transition frequency	f_T	V_{CE}= 5 V, I_C= 10mA f =30MHz	150			MHz

CLASSIFICATION OF $H_{FE(1)}$

Rank	A	B	C	D
Range	60-150	100-300	200-600	400-1000

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